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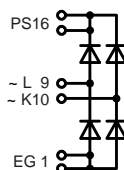
IXYS **VBE 100-06NO7**

Single Phase Rectifier Bridge
with Fast Recovery Epitaxial Diodes (FRED)
 in ECO-PAC 2

$I_{dAV} = 100 \text{ A}$
 $V_{RRM} = 600 \text{ V}$
 $t_{rr} = 35 \text{ ns}$

Preliminary data sheet

V_{RSM}	V_{RRM}	Typ
V	V	
600	600	VBE 100-06NO7



Pin arrangement see outlines

Symbol	Conditions	Maximum Ratings	
$I_{dAV} \text{ ①}$	$T_C = 85^\circ\text{C}$, module	100	A
I_{dAVM}		100	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	600 A 640 A
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	520 A 555 A
I^2t	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1800 A ² s 1720 A ² s
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1350 A ² s 1295 A ² s
T_{VJ}		-40...+150	°C
T_{VJM}		150	°C
T_{stg}		-40...+125	°C
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	t = 1 min t = 1 s	3000 V~ 3600 V~
	M_d	Mounting torque (M4)	1.5-2/14-18 Nm/lb.in.
Weight	typ.		24 g

Features

- Package with DCB ceramic base plate in low profile
- Isolation voltage 3000 V~
- Planar passivated chips
- Low forward voltage drop
- Leads suitable for PC board soldering

Applications

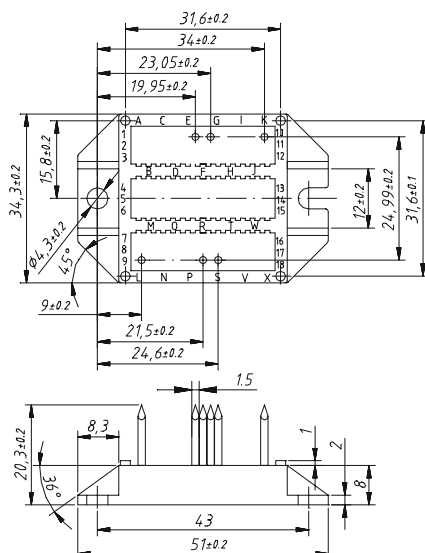
- Supplies for DC power equipment
- Input and output rectifiers for high frequency
- Battery DC power supplies
- Field supply for DC motors

Advantages

- Space and weight savings
- Improved temperature and power cycling capability
- Small and light weight
- Low noise switching

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R	$V_R = V_{RRM}$ $V_R = V_{RRM}$	$T_{VJ} = 25^\circ\text{C}$	0.1 mA
		$T_{VJ} = T_{VJM}$	2.5 mA
V_F	$I_F = 60 \text{ A}$	$T_{VJ} = 25^\circ\text{C}$	2.04 V
V_{T0}	for power-loss calculations only		1.09 V
r_T			4.3 mΩ
R_{thJC}	per diode; DC current		0.8 KW
R_{thCH}	per diode, DC current, typ.		0.2 KW
I_{RM}	$I_F = 130 \text{ A}$, -diF/dt = 100 A/μs $V_R = 100 \text{ V}$, $T_{VJ} = 100^\circ\text{C}$		6.8 A
t_{rr}	$I_F = 1 \text{ A}$; -di/dt = 300 A/μs; $V_R = 30 \text{ V}$, $T_{VJ} = 25^\circ\text{C}$	35	ns
a	Max. allowable acceleration	50	m/s ²
d_S	creeping distance on surface (pin to heatsink)	11.2	mm
d_A	strike distance in air (pin to heatsink)	9.7	mm

Dimensions in mm (1 mm = 0.0394")



Data according to IEC 60747 refer to a single diode unless otherwise stated
 ① for resistive load at bridge output.

IXYS reserves the right to change limits, test conditions and dimensions.

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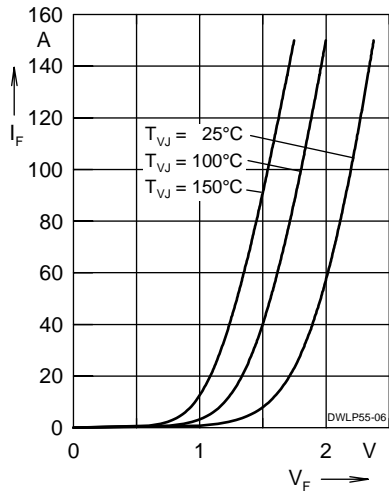


Fig. 1 Forward current I_F versus V_F

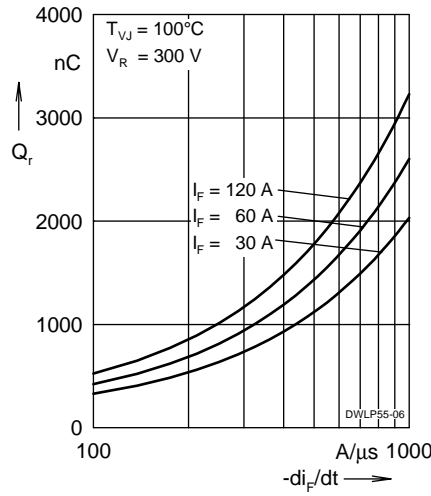


Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

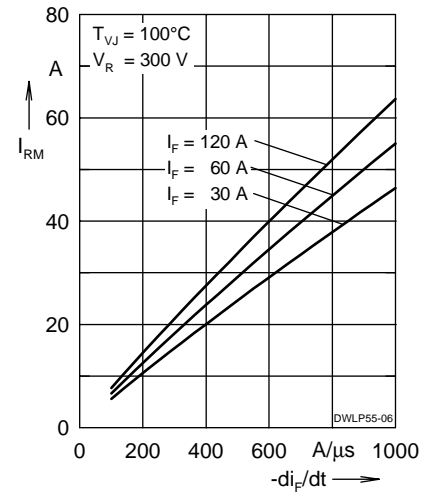


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

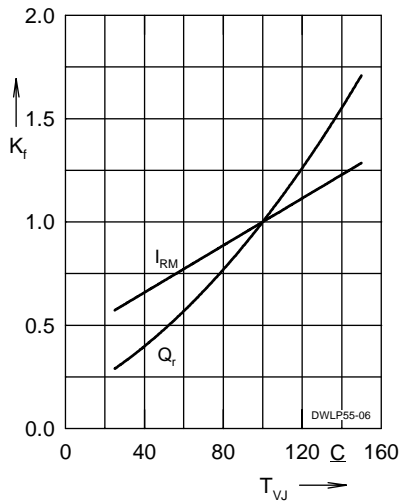


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

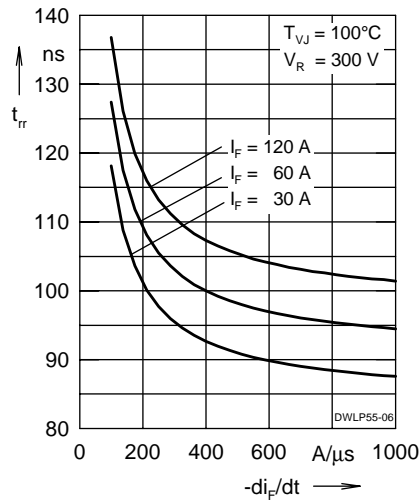


Fig. 5 Recovery time t_{rr} versus $-di_F/dt$

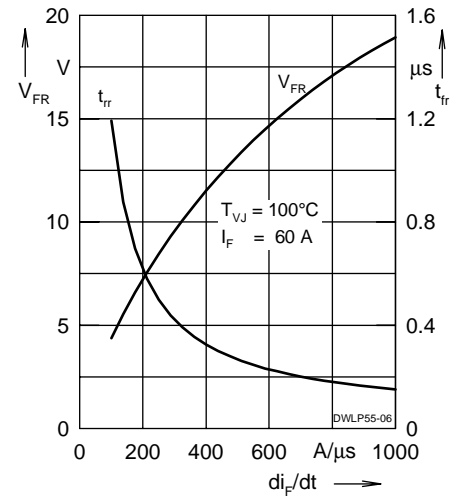


Fig. 6 Peak forward voltage V_{FR} and t_{tr} versus di_F/dt

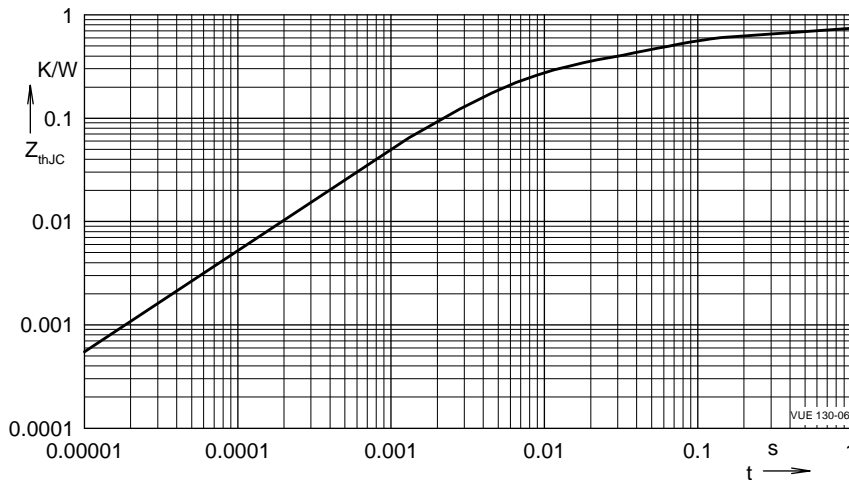


Fig. 7 Typical transient thermal resistance junction to case

NOTE: Fig. 2 to Fig. 6 shows typical values

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